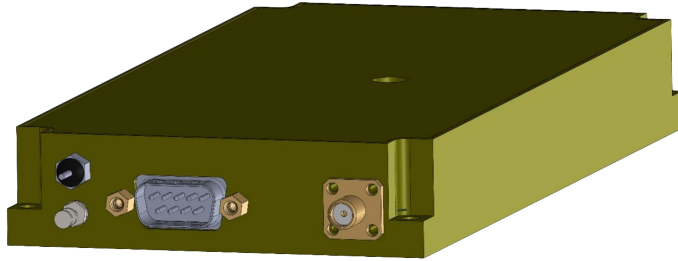


## Amplifiers up to 320W and 80 dB gain



### Product Description

UEC RF-Microwave RF predistortion amplifiers play a vital role in enhancing the performance of 3G, 4G, and 5G communication systems. In these networks, they are used to mitigate the effects of non-linearity in power amplifiers, which can lead to signal distortion and reduced efficiency. By applying predistortion techniques, these amplifiers ensure that the transmitted signals maintain high linearity, which is crucial for supporting the increased data rates and bandwidth demands of modern mobile communications.

### Typical Application

- ▶ 2G, 3G, 4G, 5G
- ▶ GSM, CDMA, LTE
- ▶ Base Stations
- ▶ Repeaters
- ▶ Private Networks

### Features

- ▶ High Linearity
- ▶ GaN and LDMOS Technology
- ▶ Class D and Doherty designs
- ▶ Psat up to 320 Watts
- ▶ Thermal Management

### Electrical Specifications ( $T_A = 25^\circ C$ )

Description	UOM	Min	Typical	Max	Notes
Frequency	GHz	.002		6.00	customer to define frequency band
Small Signal Gain	dB			+80	customer defined
Gain Flatness	±dB		TBD		bandwidth dependent
Gain Variation over Temp	±dB			3	
Saturate Power (Psat)	W			320	customer defined
Max Input Power	dBm			10	
Input Dynamic Range	dB	-40		9	customer defined
Harmonics	dBc			-20	
Rise/Fall Time	nS		10		
Spurious Out	dBc			-60	
Input VSWR	:1			1.5	
Output VSWR	:1			1.5	
Voltage Range	VDC	12		48	
Current	mA			TBD	dependent on Psat and VDC